

TDA7386

4 x 40W QUAD BRIDGE CAR RADIO AMPLIFIER

- HIGH OUTPUT POWER CAPABILITY: 4 x 45W/4Ω MAX.
 4 x 40W/4Ω EIAJ
 4 x 28W/4Ω @ 14.4V, 1KHz, 10%
 4 x 24W/4Ω @ 13.2V, 1KHz, 10%
- LOW DISTORTION
- LOW OUTPUT NOISE
- ST-BY FUNCTION
- MUTE FUNCTION
- AUTOMUTE AT MIN. SUPPLY VOLTAGE DE-TECTION
- LOW EXTERNAL COMPONENT COUNT: – INTERNALLY FIXED GAIN (26dB)
 - NO EXTERNAL COMPENSATION
 - NO BOOTSTRAP CAPACITORS

PROTECTIONS:

- OUTPUT SHORT CIRCUIT TO GND, TO V_S, ACROSS THE LOAD
- VERY INDUCTIVE LOADS
- OVERRATING CHIP TEMPERATURE WITH SOFT THERMAL LIMITER
- LOAD DUMP VOLTAGE
- FORTUITOUS OPEN GND

BLOCK AND APPLICATION DIAGRAM



FLEXIWATT25

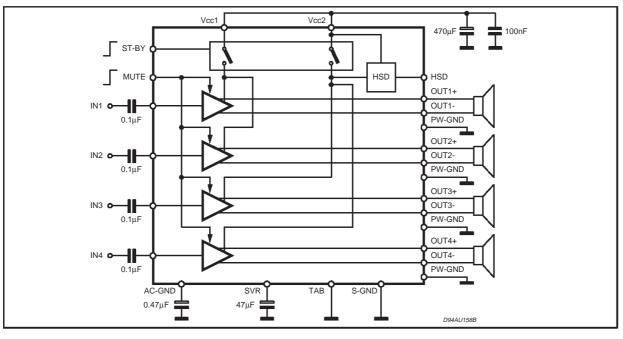
ORDERING NUMBER: TDA7386

- REVERSED BATTERY
- ESD

DESCRIPTION

The TDA7386 is a new technology class AB Audio Power Amplifier in Flexiwatt 25 package designed for high end car radio applications.

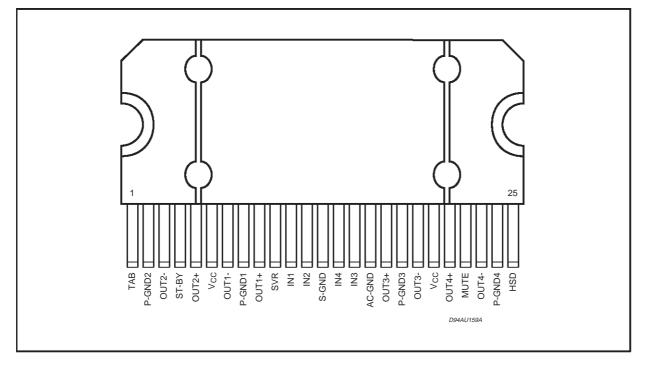
Thanks to the fully complementary PNP/NPN output configuration the TDA7386 allows a rail to rail output voltage swing with no need of bootstrap capacitors. The extremely reduced components count allows very compact sets.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Operating Supply Voltage	18	V
V _{CC (DC)}	DC Supply Voltage	28	V
V _{CC (pk)}	Peak Supply Voltage (t = 50ms)	50	V
Ι _Ο	Output Peak Current: Repetitive (Duty Cycle 10% at $f = 10Hz$) Non Repetitive ($t = 100\mu s$)	4.5 5.5	A A
P _{tot}	Power dissipation, $(T_{case} = 70^{\circ}C)$	80	W
Tj	Junction Temperature	150	°C
T _{stg}	Storage Temperature	– 55 to 150	°C

PIN CONNECTION (Top view)



THERMAL DATA

Symbol	Parameter		Value	Unit
R _{th j-case}	Thermal Resistance Junction to Case	Max.	1	°C/W

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Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
l _{q1}	Quiescent Current	$R_L = \infty$		190	350	mA
V _{OS}	Output Offset Voltage	Play Mode			±80	mV
dV _{OS}	During mute ON/OFF output offset voltage				±80	mV
Gv	Voltage Gain		25	26	27	dB
dGv	Channel Gain Unbalance				±1	dB
Po	Output Power	$\begin{array}{l} V_S = 13.2 \text{V}; \ \text{THD} = 10\% \\ V_S = 13.2 \text{V}; \ \text{THD} = 0.8\% \\ V_S = 14,4 \text{V}; \ \text{THD} = 10\% \end{array}$	22 16.5 26	24 18 28		W W W
P _{0 EIAJ}	EIAJ Output Power (*)	V _S = 13.7V	37.5	40		W
Po max.	Max. Output Power (*)	V _S = 14.4V	43	45		W
THD	Distortion	$P_o = 4W$		0.04	0.15	%
e _{No}	Output Noise	"A" Weighted Bw = 20Hz to 20KHz		50 70	70 100	μV μV
SVR	Supply Voltage Rejection	$f = 100Hz; V_r = 1Vrms$	50	75		dB
f _{ch}	High Cut-Off Frequency	$P_0 = 0.5W$	80	200		KHz
Ri	Input Impedance		70	100		KΩ
CT	Cross Talk	$ f = 1 KHz P_O = 4W \\ f = 10 KHz P_O = 4W $	60	70 60	_ _	dB dB
I _{SB}	St-By Current Consumption	$V_{St-By} = 1.5V$			100	μΑ
I _{pin4}	St-by pin Current	VSt-By = 1.5V to 3.5V			±10	μA
V _{SB out}	St-By Out Threshold Voltage	(Amp: ON)	3.5			V
$V_{\text{SB in}}$	St-By in Threshold Voltage	(Amp: OFF)			1.5	V
AM	Mute Attenuation	P _{Oref} = 4W	80	90		dB
V _{M out}	Mute Out Threshold Voltage	(Amp: Play)	3.5			V
V _{M in}	Mute In Threshold Voltage	(Amp: Mute)			1.5	V
$V_{AM \ in}$	V _S Automute Threshold	$\begin{array}{l} (Amp: Mute) \\ Att \geq 80dB; \ P_{Oref} = 4W \\ (Amp: \ Play) \end{array}$			6.5	V
		Att < 0.1 dB; P ₀ = 0.5 W		7.6	8.5	V
I _{pin22}	Muting Pin Current	V _{MUTE} = 1.5V (Sourced Current)	5	11	20	μA
		$V_{MUTE} = 3.5V$	-5		20	μΑ

ELECTRICAL CHARACTERISTICS (V_S = 14.4V; f = 1KHz; R_g = 600 Ω ; R_L = 4 Ω ; T_{amb} = 25°C; Refer to the test and application diagram, unless otherwise specified.)

(*) Saturated square wave output.

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TDA7386

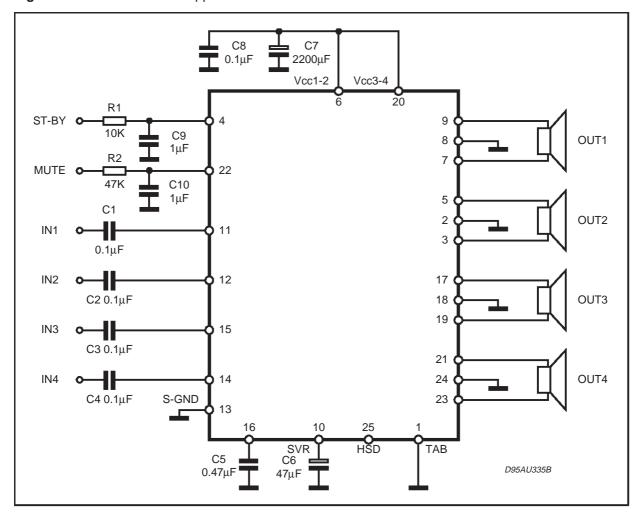


Figure 1: Standard Test and Application Circuit

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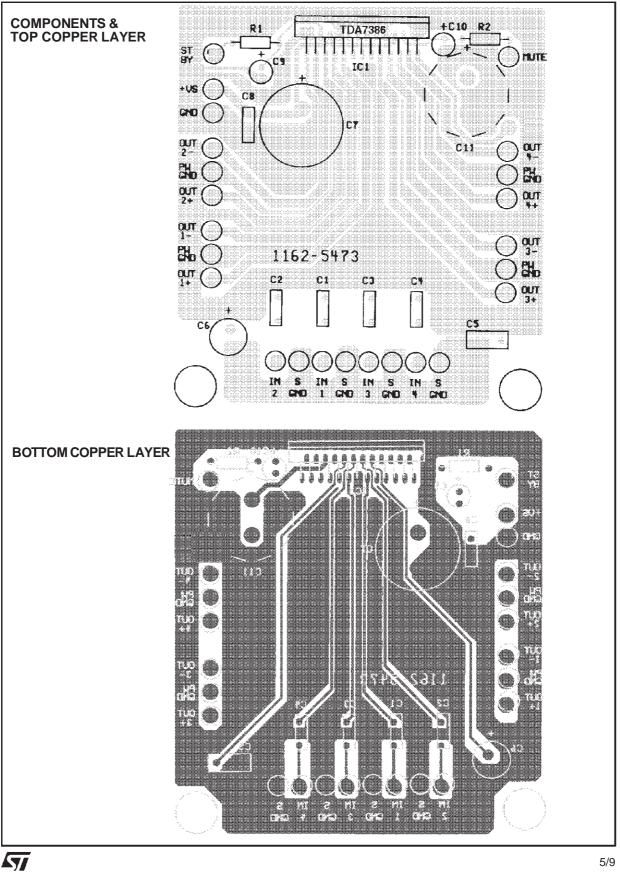


Figure 2: P.C.B. and component layout of the figure 1 (1:1 scale)

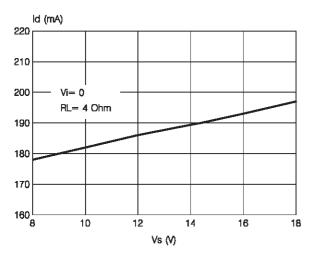
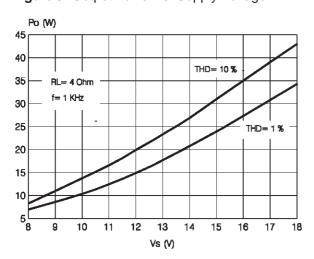
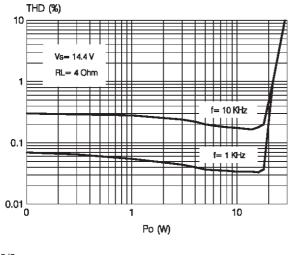


Figure 3: Quiescent Current vs. Supply Voltage

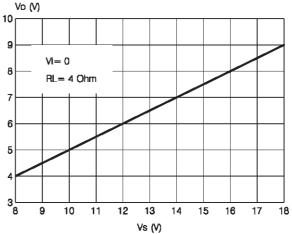


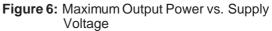


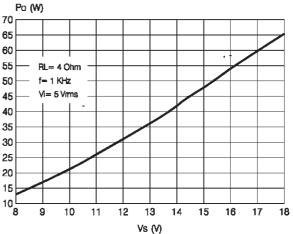




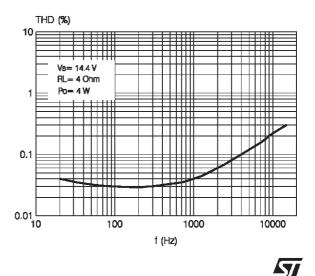












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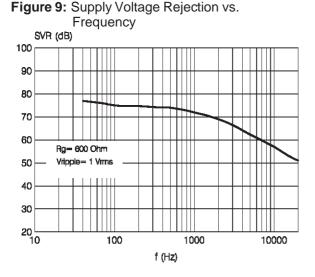
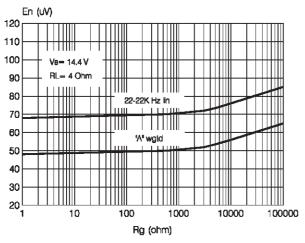


Figure 11: Output Noise vs. Source Resistance



APPLICATION HINTS (ref. to the circuit of fig. 1) SVR

Besides its contribution to the ripple rejection, the SVR capacitor governs the turn ON/OFF time sequence and, consequently, plays an essential role in the pop optimization during ON/OFF transients. To conveniently serve both needs, **ITS MINIMUM RECOMMENDED VALUE IS 10**µF.

INPUT STAGE

The TDA7386's inputs are ground-compatible and can stand very high input signals (\pm 8Vpk) without any performances degradation.

If the standard value for the input capacitors (0.1 $\mu F)$ is adopted, the low frequency cut-off will amount to 16 Hz.

STAND-BY AND MUTING

STAND-BY and MUTING facilities are both



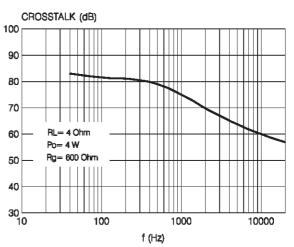
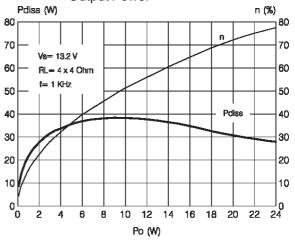


Figure 12: Power Dissipation & Efficiency vs. Output Power



CMOS-COMPATIBLE. If unused, a straight connection to Vs of their respective pins would be admissible. Conventional/low-power transistors can be employed to drive muting and stand-by pins in absence of true CMOS ports or microprocessors.

R-C cells have always to be used in order to smooth down the transitions for preventing any audible transient noises.

Since a DC current of about 10 uA normally flows out of pin 22, the maximum allowable muting-series resistance (R_2) is 70K Ω , which is sufficiently high to permit a muting capacitor reasonably small (about 1 μ F).

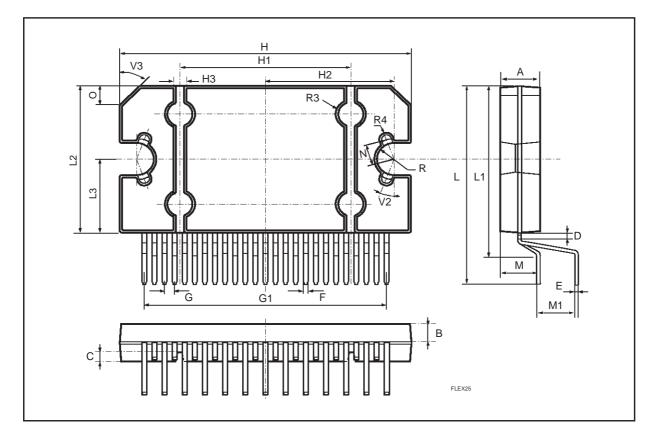
If R_2 is higher than recommended, the involved risk will be that the voltage at pin 22 may rise to above the 1.5 V threshold voltage and the device will consequently fail to turn OFF when the mute line is brought down.

About the stand-by, the time constant to be assigned in order to obtain a virtually pop-free transition has to be slower than 2.5V/ms.

TDA7386

DIM.	mm			inch			
DINI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α	4.45		4.65	0.175		0.183	
В	1.80	1.90	2.00	0.070	0.074	0.079	
С		1.40			0.055		
D	0.75	0.90	1.05	0.029	0.035	0.041	
E	0.37	0.39	0.42	0.014	0.015	0.016	
F			0.57			0.022	
G	0.80	1.00	1.20	0.031	0.040	0.047	
G1	23.75	24.00	24.25	0.935	0.945	0.955	
Н	28.90	29.23	29.30	1.138	1.150	1.153	
H1		17.00			0.669		
H2		12.80			0.503		
H3		0.80			0.031		
L	21.57	21.97	22.37	0.849	0.865	0.880	
L1	18.57	18.97	19.37	0.731	0.786	0.762	
L2	15.50	15.70	15.90	0.610	0.618	0.626	
L3	7.70	7.85	7.95	0.303	0.309	0.313	
М	3.70	4.00	4.30	0.145	0.157	0.169	
M1	3.60	4.00	4.40	0.142	0.157	0.173	
Ν		2.20			0.086		
0		2			0.079		
R		1.70			0.067		
R4		0.50			0.019		
V2	20°						
V3	45°						

Flexiwatt25



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